

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

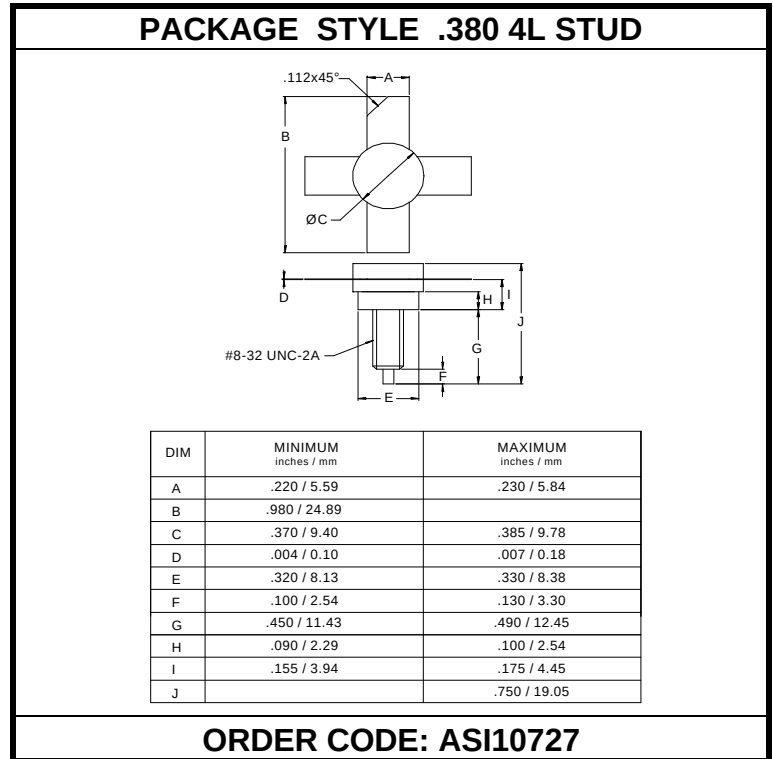
The **ASI VHB40-28S** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA	35			V
BV_{CES}	I _C = 200 mA	65			V
BV_{CBO}	I _C = 10 mA	65			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _{CE} = 30 V			10	mA
I_{CBO}	V _{CB} = 30 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 500 mA	5.0		200	---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			65	pF
P_G	V _{CE} = 28 V P _{IN} = 7.0 W f = 175 MHz	7.6			dB
η_C		60			%